

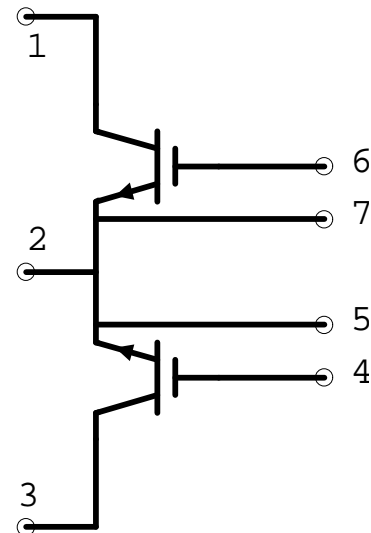
Description:

Powerex Dual Common Emitter IGBT Power Module features two common emitter IGBT's.

Features:

- Two switches - each capable of 100Amps
- Isolated Mounting
- Low Drive Requirement
- Internal Series Gate Resistors
- Isolation Material - DBC Alumina
- Baseplate Material - Copper

Schematic:



Dim	Inches Min.	Inches Max	Millimeters Min	Millimeters Max	Dim	Inches Min.	Inches Max	Millimeters Min	Millimeter Max
A	3.681	3.721	93.50	94.51	K	0.61	0.65	15.49	16.51
B	3.145	3.155	79.88	80.14	L	0.502	0.522	12.75	13.26
C	1.329	1.349	33.76	34.26	M	0.46	0.48	11.68	12.19
D	1.28	1.32	32.51	33.53	N	0.403	0.423	10.24	10.74
E	1.161	1.201	29.49	30.51	P	0.305	0.325	7.75	8.26
F	0.940	0.95	23.88	24.13	Q	0.251	0.261	6.38	6.63
G	0.901	0.911	22.88	23.14	S	---	---	M6 x 0.8	M6 x 0.8

Electrical Characteristics of Each Switch
(2 switches per module)

Part	Symbol	Parameter	Units
IGBT (each Switch)	Vces	Collector Emitter Voltage Vge=0	600 V
	Vges	Gate Emitter Voltage Vce=0	20 V
(2 Switches/Module)	Rth(j-c)	Thermal Impedance Junction to case	0.31 C/W
		Quantity of IGBT Die 10mm x 10mm per switch	1
Diode (each Switch)	Vrrm	Peak Reverse Blocking Voltage	1000 V
	trr	Reverse recovery time	TBD
(2 Switches/Module)	Qrr	Reverse Recovery charge	TBD
	Rth(j-c)	Thermal Impedance Junction to case	0.31 C/W
		Quantity of Diode Die 10mm x 10mm per switch	1
Package	Vrms	V Isolation	2000 V
		Module weight	500 g
		Max. Mounting torque M6 Mounting screw	6 Nm
		Max. Terminal torque, M6 Terminal Screw	6 Nm

600V, 100A IGBT Element Vcesat (Typical)

